

EAST - [jig.wsp:1]

FileViewEditToolsWindowHelp

Active

L1: (33216) gate and floating and control

L2: (16657) 1 and gate.clm.

L3: (6379) 2 and flash

L4: (5286) 3 and (floating or control).clm.

L5: (4423) 4 and (tunnel or oxide)

L6: (2494) 5 and dielectric

L7: (1363) 6 and oxidation

L8: (13) 7 and (dry adj oxidis\$)

L9: (7) 8 and ((sidewall\$1) or (side adj wall\$1))

L10: (0) 5 and C\$1H\$1C1\$1

L11: (20) 5 and (dry adj oxidis\$4)

L12: (13) 11 and (sidewall or (side adj wall))

L13: (0) 5 and oxygen and TCA

L14: (15712) silicon adj germanium or (SiGe)

L15: (5830) 14 and plasma

L16: (2489) 15 and (hydrogen or H\$1)and (Ar or argon)

PrintBrowseQueueClear

D8:USPAT:US-PCPU8

Default operator:OR

22 and (H\$1 or hydrogen).clm. and (argon.clm. or Ar.clm.)

USP term

USP term

Image

Text

HTML

|   | U                        | 1                                   | Document ID       | Issue Date | Pages | Title   | Current OR | Current XRef                 | Retrieval C | Inventor                | S                                   | C                        | P                        | 3                        | 9                        | NUM     |
|---|--------------------------|-------------------------------------|-------------------|------------|-------|---|------------|------------------------------|-------------|-------------------------|-------------------------------------|--------------------------|--------------------------|--------------------------|--------------------------|---------|
| 1 | <input type="checkbox"/> | <input type="checkbox"/>            | US 20010013607 A1 | 20010816   | 35    | FABRICATION METHOD FOR A THIN FILM SEMICONDUCTOR DEVI | 257/66     | 257/72;<br>257/E21.101;      |             | MIYASAKA, MITSUTOSHI    | <input checked="" type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 2001 |
| 2 | <input type="checkbox"/> | <input checked="" type="checkbox"/> | US 6187682 B1     | 20010213   | 15    | Inert plasma gas surface cleaning process performed i | 438/694    | 204/192.3;<br>257/E21.165;   |             | Denning, Dean J. et al. | <input checked="" type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 6    |
| 3 | <input type="checkbox"/> | <input type="checkbox"/>            | US 6017779 A      | 20000125   | 32    | Fabrication method for a thin film semiconductor devi | 438/149    | 257/E21.101;<br>257/E21.202; |             | Miyasaka, Mitsutoshi    | <input checked="" type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | US 6    |

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Ready

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